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(71)Name of Applicant :

1)Chitkara University

Address of Applicant :Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India Rajpura -----

2)Chitkara Innovation Incubator Foundation

Name of Applicant : NA

Address of Applicant : NA

(72)Name of Inventor :

1)Ms.Shivani

Address of Applicant :JRF, Department of Electronics & Communication Engineering, Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India Rajpura -----

2)Dr. Jaya Madan

Address of Applicant :Assistant Professor, Department of Electronics & Communication Engineering, Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India Rajpura -----

3)Dr. Rahul Pandey

Address of Applicant :Assistant Professor, Department of Electronics & Communication Engineering, Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India Rajpura -----

(57) Abstract :

ABSTRACT SOLAR CELL WITH DOPED SURFACE INVERSION LAYER AND METHOD OF MANUFACTURING

THEREOF The present disclosure describes a solar cell (100) comprising an electrode (102), a bulk FeS₂ layer (104) deposited on the electrode (102), having a predefined bandgap, and an acceptor-doped surface inversion layer SIL (106). The surface inversion layer SIL (106) is formed on the bulk FeS₂ layer (104), creating an internal p-n junction, wherein the bandgap of the SIL (106) is equivalent to that of the bulk FeS₂ layer (104). FIG. 1

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